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(54) **CHARGE-BIASED MEM RESONATOR**

MEM-RESONATOR POLARISIERT DURCH DIE LADUNG

RÉSONATEUR MEM POLARISÉ PAR LA CHARGE

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- **AYAZI F ET AL: "HIGH ASPECT-RATIO COMBINED POLY AND SINGLE-CRYSTAL SILICON (HARPSS) MEMS TECHNOLOGY" JOURNAL OF MICROELECTROMECHANICAL SYSTEMS, IEEE SERVICE CENTER, PISCATAWAY, NJ, US, vol. 9, no. 3, 1 September 2000 (2000-09-01), pages 288-294, XP001010966 ISSN: 1057-7157**
- **NGUYEN C T-C: "Vibrating RF mems for next generation wireless applications" CUSTOM INTEGRATED CIRCUITS CONFERENCE, 2004. PROCEEDINGS OF THE IEEE 2004 ORLANDO, FL, USA OCT. 3-6, 2004, PISCATAWAY, NJ, USA, IEEE, 3 October 2004 (2004-10-03), pages 257-264, XP010742287 ISBN: 0-7803-8495-4**

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Description

[0001] This invention relates to MEM resonators and devices incorporating such resonators as well as methods of operating the same.

[0002] Microelectromechanical (MEM or MEMS) resonators are known and are notable for high on-chip Q-factors at RF frequencies. MEM resonators convert electrical signals into extremely low-loss mechanical vibration of a vibrating element, and convert the vibration back into electrical signals. They produce an output only if the input is close to the resonant frequency of the moveable element. They can be used as narrow band filters which can be incorporated into oscillators, or VCOs for example. Previously such functions often used components such as SAW filters or quartz resonators. Quartz resonators have been used as frequency selective elements in oscillator circuits (e.g. Colpitts Oscillator, Pierce Oscillator). Unfortunately quartz resonators are costly, bulky discrete components which cannot be integrated easily using fabrication techniques that are compatible with modern IC processes. Hence MEM resonators are of interest to reduce packaging/assembly cost and component count, reduce impedance matching issues, and parasitics that can significantly affect performance for RF applications. This can lead to consolidating all of the RF/analog/digital components onto a single wireless-enabled chip, commonly called RF system-on-a-chip (SoC). This can use modem CMOS processes for example, on N or P type monocrystalline semiconductor wafers. Various resonator geometries are known for the vibrating element and the electrodes, including vibrating elements in the form of clamped beams, cantilevers and discs, and arrangements with multiple vibrating elements.

[0003] It is known from US patent application 20030052742 to provide MEM resonators comprising at least two vibratable members that are closely spaced relative to a wavelength associated with their vibrating frequency, and driven to vibrate one-half a vibration period out of phase with each other, i.e. to mirror each others motion. Driving the vibratable members as stated leads to destructive interference effects that suppress leakage of acoustic energy from the vibratable members into the die, and improve the Q-factor of the resonator. Vibratable members in the form of vibratable plates are formed by deep anisotropic etching one or more trenches in the die, using a similar process to that used to form integrated capacitors for CMOS based memory.

[0004] It is known from WO 03/023957 that high Q mechanical resonators operated in the 100+ MHz range have some limitations. Additionally, the upper frequency range of these high Q resonators is low restricting their use for some applications. Further these high Q resonators are difficult to fabricate and have a relatively large mass. Accordingly this document suggests the resonator includes a member with an embedded charge, at least one input electrode, at least one output electrode, and at least one common electrode. The input and output electrodes are spaced from and on substantially opposing sides of the member from the common electrode. At least one of the member and the input and output electrodes is movable with respect to the other. During manufacture, electrons are injected into the member with an electron gun to deposit an embedded charge, although other techniques for storing embedded charge in the member can also be used, such as applying an electrical bias across the member sufficient to cause electron injection, ballistic injection, polarization, and high field injection. The same techniques can be used to store an embedded charge in a member formed of dielectric or formed as a charged floating conductor.

[0005] There remains a need for improved devices.

[0006] Ayazi F et al discuss high aspect-ratio combined poly and single-crystal silicon (HARPSS) MEMS technology in Volume 9, Nr: 3, Pages 288-294 of the Journal of Microelectromechanical Systems (20000901 IEEE Service Center, Piscataway, NJ, US - ISSN 1057-7157).

[0007] Nguyen Clark T.-C presented vibrating RF MEMS for next generation wireless applications at the Custom Integrated Circuit Conference, 2004 (Proceedings of the IEEE 2004, Orlando, FL, USA, October 3-6, 2004, Piscataway, NJ, USA, IEEE, 3 October 2004, pages 257-264. ISBN: 0-7803-8495-4).

[0008] Nguyen Clark T-C also discloses several MEMS-based methods and architectures which utilize vibrating micromechanical resonators in United States Patent Application Publication No. US 2001/033119 A1.

[0009] A radial bulk annular resonator using MEMS technology is presented United States Patent Application Publication No. US 2004/232501 A1.

[0010] United States Patent No. US 6,621,134 discloses a vacuum sealed RF/microwave microresonator.

[0011] An object of the invention is to provide improved MEM resonators and devices incorporating such resonators as well as methods of controlling same.

[0012] According to a first aspect, the invention provides: - a resonator according to claim 1.

[0013] The resonator can have input and output electrodes. Moreover the present invention does not require a common electrode.

[0014] The above arrangements can help enable the amount of charge to be maintained against charge leakage. It can also enable the amount of charge to be reduced so that pull in forces to the substrate are reduced, thus reducing problems of stiction. Advantages of using stored charge rather than a voltage source to bias the device, can include reduced power consumption, less need for high voltage power supplies, and more linear output current with displacement of the vibrating element. Reducing such non-linear effects can lead to a higher Q factor and so narrower band filtering characteristics. This is particularly true under certain operation conditions, where the electrical non-linearities dominate over the mechanical non-linearities. An additional feature of the present invention is the charge adjuster comprising a charge reservoir coupled to the charged electrode or

charged element. This is a particularly straightforward way of maintaining charge against leakage. Since the reservoir can store much more charge than the electrode alone, a given leakage will have a proportionally much smaller effect on the amount of charge left on the combined reservoir and electrode.

[0015] Another such additional feature is the charged electrode or charged element being an input or output electrode. As opposed to having a common electrode or vibrating element being charged, this can bring some of the benefits of charged electrodes, being reduced power consumption, less need for high voltage power supplies, and more linear output current with displacement of the vibrating element, while reducing the drawbacks of pull in forces on the vibrating element if it is charged.

[0016] Another such additional feature is charged electrodes being arranged on both sides of the vibrating element. This can improve linearity of the device characteristics. Electrodes on opposing sides is not necessarily an essential requirement for the invention. Another such additional feature is the charge reservoir comprising a decoupling capacitor in an input or output path to or from an electrode.

[0017] Another additional feature for a dependent claim is the vibrating element being coupled to earth. This can enable the vibrating element to be used as an output electrode in two electrode, one gap arrangement, or used with charged electrodes on one or both sides, for example.

[0018] Another additional feature for a dependent claim is the vibrating element being coupled to earth via a switch. This can enable any charge on the vibrating element to be reduced before operation or at any time. A further advantage of using switches is that they can have low leakage. Also, although an alternative without a switch is simpler, it can lead to some non linearity in output.

[0019] Another additional feature is a second charged electrode.

[0020] Another additional feature is the second charged electrode being charged to a different polarity. This can reduce the motional impedance of the vibrating element.

[0021] Another additional feature is a controller arranged to control the first and/or second switches to be closed to precharge the resonator and to be open during operation.

[0022] Another additional feature is the first and/or second switch comprising a MEM switch.

[0023] Other aspects of the invention include methods of controlling the resonator, and an integrated circuit comprising the resonator.

[0024] Any of the additional features can be combined together and combined with any of the aspects. Other advantages will be apparent to those skilled in the art, especially over other prior art. Numerous variations and modifications can be made without departing from the claims of the present invention. Therefore, it should be clearly understood that the form of the present invention is illustrative only and is not intended to limit the scope of the present claims.

[0025] How the present invention may be put into effect will now be described by way of example with reference to the appended drawings, in which:

Fig. 1 shows a conventional resonator,

Figs. 2 to 7 show resonators according to embodiments of the invention,

Figs. 8 and 9 show an example of a MEM switch for use with the embodiments,

Fig. 10 shows an example of a floating gate device for use as a switch, and

Fig. 11 shows an example of a resonator structure for use in the embodiments.

[0026] The present invention will be described with respect to particular embodiments and with reference to certain drawings but the invention is not limited thereto but only by the claims. The drawings described are only schematic and are non-limiting. In the drawings, the size of some of the elements may be exaggerated and not drawn on scale for illustrative purposes. Where the term "comprising" is used in the present description and claims, it does not exclude other elements or steps. Where an indefinite or definite article is used when referring to a singular noun e.g. "a" or "an", "the", this includes a plural of that noun unless something else is specifically stated.

[0027] The term "comprising", used in the claims, should not be interpreted as being restricted to the means listed thereafter; it does not exclude other elements or steps. Thus, the scope of the expression "a device comprising means A and B" should not be limited to devices consisting only of components A and B. It means that with respect to the present invention, the only relevant components of the device are A and B.

[0028] Furthermore, the terms first, second, third and the like in the description and in the claims, are used for distinguishing between similar elements and not necessarily for describing a sequential or chronological order. It is to be understood that the terms so used are interchangeable under appropriate circumstances and that the embodiments of the invention described herein are capable of operation in other sequences than described or illustrated herein.

[0029] Moreover, the terms top, bottom, over, under and the like in the description and the claims are used for descriptive purposes and not necessarily for describing relative positions. It is to be understood that the terms so used are interchangeable under appropriate circumstances and that the embodiments of the invention described herein are capable of operation in other orientations than described or illustrated herein.

[0030] Figure 1 shows schematically a conventional voltage biased MEMS resonator. A vibrating element 10 is sandwiched between two electrodes 20, 30. The

squares 3, 5 indicate the anchors by which the vibrating element is fixed, e.g. to a substrate. The resonator is attached to or is part of the substrate.

[0031] The resonator needs a high voltage supply 8 to bias the electrodes 20, 30 with a high DC voltage to achieve a high electric field in the gaps 9. An alternating voltage source Vin 10 is shown as an input 7, and an output 4 is measured in terms of a current Iout (6) induced by the vibrating element 10.

[0032] Figure 2 shows schematically a first embodiment of a charge biased resonator in accordance with the present invention. The resonator is attached to or is part of a substrate, e.g. a semiconductor substrate. As described above, the squares 3, 5 indicate the anchors by which the resonating element is fixed, e.g. to the substrate. Clearly other geometries are conceivable for the vibrating element and its anchor or anchors, as discussed above, and it is not intended to limit the present invention to a particular geometry. Compared to Figure 1, this arrangement differs in that biasing of the resonator is done with a fixed charge instead of a fixed voltage. Accordingly the beam 10 is not connected to a DC voltage supply during use. An advantage of this method is that the resonator does not need a separate high DC voltage source 8 and once biased, e.g. during production, the biasing, and therefore the frequency of the resonance is not susceptible to variations in level of the DC voltage supply during operation. This allows more accurate tuning of its resonance frequency.

[0033] If the same bias voltage is used the motional resistance of the charge biased resonator is at least approximately equal to a voltage biased resonator. The gap 9 between the resonator beam 10 and the left electrode is g + x, the gap 9' between the beam and the right electrode is g-x (x is the displacement from equilibrium). A charge Qdc = Vdc 2 A ε_0/g is applied when the switch is closed. The ac voltage Vin=0 when applying the bias charge. In accordance with a further embodiment, whereas previously the stored charge was inserted only during manufacture, e.g. by an electron gun, now a charge adjuster is provided to add to or reduce the stored charge, in the form of a voltage supply 8 coupled by a switch 11. Since a switch 11 is provided, the pre-charging can be repeated. Before operation the resonator is pre-charged, e.g. the switch 11 is closed, Vin=O V. During operation the switch 11 is open. Ideally no charge leaks away, but in practice there will be some leakage. Accordingly, the switch 11 can be closed briefly to refresh the charge. This can be carried out in the field such as at switch on or initialization of a system, or less often, such as when maintenance is carried out, or when a fault is detected.

[0034] Charge-biasing the resonator by adding charge to the vibrating beam 10 as in Figure 2 has one drawback. When much charge is accumulated on the free beam 10, a force might develop between the substrate and the free beam 10. This effect can lead to deformation and eventually even pull-down and stiction of the resonator. Accordingly, in other embodiments, the vibrating element 10 is held to ground potential. In the embodiment of Figure 3, electrodes at either side of the element 10 are input 20 and output 30 electrodes respectively, and are both used to store a charge, to charge bias the resonator. A charge adjuster in the form of a voltage supply 8; 8' coupled by a first switch 11; 11' is provided for each electrode 20, 30 separately. A decoupling capacitor C is provided to keep the high charging voltage from spreading to other parts of the circuit, e.g. at both input and output. The decoupling capacitors C can each act as a charge reservoir, or other capacitors can be provided for this purpose.

[0035] The potential on the vibrating element 10 is kept low by a coupling to a substrate (assumed to be at ground potential) or to a ground electrode via a second switch 15. Before operation the resonator is pre-charged and all switches 11, 11'; 15 are closed. During operation all switches 11, 11'; 15 are open. It can be shown that the operation of the resonator in Figure 3 is identical to that of Figure 2, except for the effect of the two series decoupling capacitors C. In the limit that the capacitance of C is infinite, both charge biased resonators have the same motional impedance, the resonator in Figure 3 however does not suffer from pull-in forces towards the substrate.

[0036] Another advantage of using a charge reservoir is that it can be used as a buffer to diminish the effect of small leakage currents. As the capacitors C can store much more charge than the resonator itself (which has a capacitance of only A ε_0/g), the amount of charge stored by the decoupling capacitors can be made very much larger. Therefore leakage currents will have a much larger impact of the resonator of Figure 1 or 2 than on that of Figure 3.

[0037] A notable advantage of the arrangements of Figures 2 and 3 is the linear response of the electrical parts, although there may still be some non linearity's from mechanical causes. It can be shown that the charge biased resonator is more linear than a voltage biased device. Notably there are three sources of non linearity in a voltage biased case. The actuation force is proportional to a square of (Vdc + Vin). Secondly, the force is inversely proportional to a square of (g + x). Thirdly, the output current is not linear to the displacement. In contrast, for the charge biased device, Iout = c(ω) * Vin , where c is independent of Vin. So only mechanical nonlinearities are left. Alternative implementations of the charge biased resonator with charge reservoir are also possible, however some of these do not have the same advantage of linearity. Examples are shown in Figures 4-7. Note that the resonators in Figures 4 and 6 only require one gap, which enables a simpler more compact construction.

[0038] Figure 4 shows a charge-biased resonator with one gap 9. Compared to Figure 3, the output electrode 30 has been removed, and the vibrating element 10 is used as the output electrode. It is coupled to an output via a decoupling capacitor C. The potential of the vibrating element 10 is precharged to ground using a switch

15 as before.

[0039] Figure 5 shows a charge-biased resonator, with the vibrating element 10 fixed at ground potential without needing a second switch 15. Otherwise this is comparable to the embodiment of Figure 3, but slightly simpler. Note that this configuration might show some non-linearity, e.g. in contrast to Figure 3. Nevertheless, no DC voltage source is required after pre-charging it.

[0040] Figure 6 shows an embodiment of a charge-biased resonator with one gap 9.

This is similar to the embodiment of Figure 4, but there is no second switch 15 to precharge the vibrating element 10 to ground. Hence there is also no need for a decoupling capacitor C on the output side.

[0041] Figure 7 shows an embodiment similar to that of Figure 4, with one gap 9, but in this case the vibrating element 10, used as the output electrode, is precharged using a voltage source 8' coupled via a switch 11'. It is charged to an opposite polarity to the charging of the other electrode 20 on the other side of the gap 9 by a voltage source 8 and a switch 11. Also note that the motional impedance of the resonator in Figure 7, is 4 times lower than that of the resonators in Figures 1-6 (which all have the same motional impedance if g>>x and Vdc>>Vin). Note that this reduction also occurs for a voltage biased resonator (all switches are closed). A disadvantage of the configuration in Figure 7 is again that a pull in force might develop between substrate and resonator (the resonator is at elevated potential).

[0042] An alternative to using a switched voltage source to apply charge to a charge biased resonator is by doing this during production by applying the charge with a needle or probe on the resonator or into the charge reservoir. The needle can be removed and if the charge leakage is sufficiently low, the charge will stay in the reservoir. If charge leakage is too high an alternative implementation might be to use the switches which, once in a while connect the resonator or the reservoir to a voltage source to restore the charge. An example of a switch using MEM technology is shown in Figures 8 and 9. In Figure 8 black areas are conducting electrodes. These Figures show two schematic views of a galvanic MEMS switch and how to connect it to the vibrating element or electrode of the resonator. Figure 8 shows the switch has two driving electrodes 18, 19 which can be forced together by application of a drive voltage, to overcome a bias spring force k. This causes closure of a pair of switch contacts 13; 14, 15. One switch contact 14 can be coupled to a Vdc voltage supply, and the other switch contact 13 to the resonator or charging reservoir R, e.g. vibrating element or electrode, as desired, according to the arrangements described above. Electrodes 13, 18 are mounted on an insulating carrier C. When the switch closes an electrical connection is made between the charging voltage and the resonator/charge reservoir. Figure 9 shows a three dimensional view of a possible construction of the switch in which GC is a galvanic contact, R is the resonator and HVDc is the high voltage connection for charging. Other geometries are possible. MEMS switches typically switch at voltages between 2-300 V, depending on the design. A typical value is 40 V. Because they have very low leakage currents they are very suitable to charge the resonator.

[0043] A transistor could be used, such as a normal FET or DMOS transistor for the switch, but for many applications the leakage currents are too high. Another example is a flash, OTP, or EPROM non-volatile memory transistor, connecting the resonator to the floating gate electrode. Electron injection can take place by CHEI (Channel Hot Electron Injection) or by Fowler Nordheim Tunneling (FN). Figure 10 shows a schematic view of a typical non-volatile memory transistor. It has a substrate 27, a source 23, a drain 25, a dielectric layer 22, a floating gate 24 and a control gate 21. Charge can be injected in the floating gate 24 by applying the following voltages: typical values are: source=0V drain=5V, Control gate =10V. Typical thickness of the dielectric between substrate and floating gate is 10 nm. Typical charge retention times of a floating gate can be very long. For example a 10 nm SiO_2 gate oxide with a potential of 4V can take 10^{20} (10^{20}) years before 10% of its charge leaked away (see G. Iannaccone and S. Gennai, Proc. 7th Int. Workshop on Computational Electronics, Glasgow 2000, p. 153, ISBN/ISSN 0-85261-704-6). For general information on non-volatile transistors see e.g.: http://www-ee.eng.hawaii.edu/~msmith/ASICs/HTML/Book2/CH04/CH04.3.htm

[0044] Another possibility is a vacuum tube, e.g. a MEMS triode. For an example of a MEMS vacuum triode see Applied Physics Letters -- May 20, 2002 -- Volume 80, Issue 20, pp. 3820-3822. The resonator or the charge reservoir could be connected to the anode of the triode. Another possibility is to use a (MEMS) fuse, by applying the charge and melting the fuse afterwards. Note that with this method the charge cannot be refreshed later. Finally another alternative is to use a corona discharge, e.g. similar to the way in which electrets are charged.

[0045] An example of a method of manufacturing a resonator structure is described briefly below with reference to Figure 12.

[0046] In Figure 12A an SOI wafer comprises a p-doped silicon layer (pSi) and insulating silicon dioxide layer (SD), a silicon substrate (Si) and an aluminum metal layer (MET) is sputter deposited onto the wafer. This layer can have a resistivity of 3 microohm.cm. The metal layer is patterned by conventional lithographic techniques. As shown in Figure 12B a lithographic resist mask (TRE) is applied and patterned followed by etching of two or more deep trenches into the upper silicon layer until the SiO_2 layer is reached, e.g. as an etch stop. As shown in Figure 12C the resist is removed. As shown in Figure 12D the SiO_2 is selectively etched away, e.g. using buffered oxide etchant (BOE), via access through the trenches. This leaves the resonator beam anchored to the silicon and suspended between two edges faces of silicon semiconductor which can act as the electrodes.

[0047] Implementation examples of the resonator structure can use conventional MEMS resonator structures, an example is illustrated in Figure 11 which shows an SEM picture from "Sensors and Actuators", A 97-98 (2002), pp. 497-502. This shows a vibrating element in the form of a beam resonator R, and anchored at each end. Electrodes E, F are shown on either side. The anchor supports and outer parts of the electrodes are metallized in this example. The dimensions make it suitable for operation at around 14Mhz. Note that to operate the devices as charge biased resonator, they need to be connected in different ways as illustrated above for example. For implementations examples of a one gap resonator see the resonators in IEEE ELECTRON DEVICE LETTERS, VOL. 25, NO. 4, APRIL 2004, p. 173 and "Sensors and Actuators", A 101 (2002), pp. 1-9. In a typical implementation example, using a 30V charge voltage, without special precautions to prevent leakage, the charge is likely to remain on the resonator for many hours. The vibrating element can be conducting or the vibrating element can be an isolator. When the vibrating element is a charged isolator one can refer to having an electret (as used in microphones).

[0048] If measures are taken such that charge does not leak away, one can completely leave out the chargepump/dc-dc-converter (for generating the very high voltage), and the circuit becomes very simple/cheap. Charge could for example be applied to the vibrating element during manufacturing (using electron guns/probe needles/etc). This is one embodiment of the invention. If charge does leak away, there is the situation where the chargepump/dc-dc converter only needs to be active once in a while, which is also advantageous because of a power saving. This is another embodiment of the invention. Additional charge reservoir capacitors are possible at various places. As discussed above, when charge leaks away from the vibrating element or from the electrodes, charge from these capacitors will fill up (and thus compensate) for the leaked charge. Basically there are three main options: 1) Extra capacitor coupled to electrodes 2) Extra capacitor coupled to the vibrating element 3) Extra capacitors coupled to electrodes and to the vibrating element.

[0049] Charge leakage can be prevented/reduced by packaging the resonator in a vacuum package. This has the advantage of allowing a sufficiently high Q-factor.

[0050] Applications and uses of these MEMS resonator include oscillators (for frequency reference signals) or filters in integrated circuits, including any applications of SAW/BAW filters.

[0051] To summarize, one of the main advantages of the charge biased resonator is the fact that no DC voltage source is required during operation. The resonator thus only needs to be pre-charged before operation. If charge-leakage can be prevented it thus only needs to be pre-charged once during production allowing the resonance frequency to be tuned to the right value at the same time. The absence of a DC voltage source also implies that the energy consumption of the resonator becomes zero. The charge biased resonator can therefore be considered as a purely passive device (like a quartz crystal).

[0052] Charge biasing has an other advantage, namely that the resonator becomes linear in all events, even if the conditions Vdc>>Vin and g»x are not satisfied. Electrical non-linearities are therefore excluded and only mechanical non-linearities remain. This can simplify design or increase Q value. Notably it is clear that the biasing does not necessarily have to be performed on the vibrating element itself but can be applied to electrodes using an external charge reservoir. Some advantages are:

- No force between substrate (at GND potential) and resonator, thus reduced risk of stiction.
- Charge reservoirs act as a charge buffer which strongly reduces the effect of leakage currents on the resonator operation and can thus strongly increase the functional lifetime of the resonator.
- Possibly simpler implementation of a leakage free device.

[0053] Some of the implementations can also be operated as voltage biased resonators (by keeping all switches closed).

Claims

1. A resonator comprising a vibrating element (10) and a first electrode (20) arranged to cause the element to vibrate according to an input signal (V_{IN}), and to generate an output signal (I_{OUT}) according to the vibration, at least one of said first electrode and the vibrating element being arranged to store an electric charge during operation of the resonator
   whereby at least one of said first electrode and the vibrating element comprises a charge adjuster arranged to add to or reduce the stored charge,
   and **characterised in that** the charge adjuster comprises a voltage source (8) coupled by a first switch (11) to the first charged electrode (20) or the charged element (10),
   and **in that** the first switch (11) is adapted so that the first charged electrode (20 or the charged element (10) is disconnected from the voltage source (8) during operation of the resonator.

2. The resonator of claim 1, the charge adjuster comprising a charge reservoir coupled to the first charged electrode or the charged element.

3. The resonator of any of claims 1 or 2, the first charged electrode (20) or the charged element (10) being an input (7) or output (4) electrode.

4. The resonator of claim 2, the charge reservoir comprising a decoupling capacitor (C) in an input or out-

put path to or from the charged electrode.

5. The resonator of any preceding claim, the vibrating element (10) being electrically coupled to a substrate or to a ground electrode.

6. The resonator of claim 5, the vibrating element (10) being electrically coupled to the substrate or to the ground electrode via a second switch (15).

7. The resonator of any preceding claim having a second charged electrode (30).

8. The resonator of claim 7, having the first and the second electrodes (20,30) arranged on both sides of the vibrating element (10).

9. The resonator of claim 7 or 8, the second charged electrode (30) being charged to a different polarity.

10. The resonator of claim 1 and having a controller arranged to control the first switch to be closed to precharge the resonator and to be open during operation of the resonator.

11. The resonator of claim 6 and having a controller arranged to control the second switch (15) to be closed to precharge the resonator and to be open during operation of the resonator.

12. The resonator of any preceding claim, the first switch (11) comprising a MEM switch.

13. The resonator of any preceding claim depending on claim 6, the second switch (15) comprising a MEM switch.

14. An integrated circuit comprising the resonator of any preceding claim.

15. A method of controlling the resonator of any of claims 1 to 13, having the step of controlling the first switch (11) to precharge the first charged electrode.

Patentansprüche

1. Ein Resonator, welcher ein vibrierendes Element (10) und eine erste Elektrode (20) aufweist, welche eingerichtet ist, um das Element zu veranlassen, gemäß dem Eingangssignal (V_{IN}) zu vibrieren, und um ein Ausgangssignal (I_{OUT}) gemäß der Vibration zu generieren, wobei zumindest eines von der ersten Elektrode und dem vibrierenden Element eingerichtet ist, um eine elektrische Ladung während eines Betriebs des Resonators zu speichern, wobei zumindest eines von der ersten Elektrode und dem vibrierenden Element einen Ladungsanpasser aufweist, welcher eingerichtet ist, Ladung zu der gespeicherten Ladung zu addieren oder die gespeicherte Ladung zu reduzieren,
und **dadurch gekennzeichnet, dass** der Ladungsanpasser eine Spannungsquelle (8) aufweist, welche mittels eines ersten Schalters (11) an die erste geladene Elektrode (20) oder das geladene Element (10) gekoppelt ist, und dadurch, dass der erste Schalter (11) angepasst ist, so dass die erste geladene Elektrode (20) oder das geladene Element (10) von der Spannungsquelle (8) während des Betriebs des Resonators getrennt wird.

2. Der Resonator gemäß Anspruch 1, wobei der Ladungsanpasser ein Ladungsreservoir aufweist, welches an die erste geladene Elektrode oder das geladene Element gekoppelt ist.

3. Der Resonator gemäß irgendeinem der Ansprüche 1 oder 2, wobei die erste geladene Elektrode (20) oder das geladene Element (10) eine Eingangs- (7) oder Ausgangs- (4) Elektrode ist.

4. Der Resonator gemäß Anspruch 2, wobei das Ladungsreservoir eine Entkopplungskapazität (C) in einem Eingangs- oder Ausgangspfad zu oder von der geladenen Elektrode aufweist.

5. Der Resonator gemäß irgendeinem vorherigen Anspruch, wobei das vibrierende Element (10) elektrisch an ein Substrat oder an eine Masseelektrode gekoppelt ist.

6. Der Resonator gemäß Anspruch 5, wobei das vibrierende Element (10) elektrisch an das Substrat oder an die Masseelektrode über einen zweiten Schalter (15) gekoppelt ist.

7. Der Resonator gemäß irgendeinem vorherigen Anspruch, welcher eine zweite geladene Elektrode (30) hat.

8. Der Resonator gemäß Anspruch 7, welcher die erste und die zweite geladene Elektrode (20, 30) auf beiden Seiten des vibrierenden Elements (10) angeordnet hat.

9. Der Resonator gemäß Anspruch 7 oder 8, wobei die zweite geladene Elektrode (30) auf eine unterschiedliche Polarität geladen ist.

10. Der Resonator gemäß Anspruch 1 und welcher einen Controller hat, welcher eingerichtet ist, um den ersten Schalter zu steuern, geschlossen zu werden, um den Resonator vorzuladen, und während des Betriebs des Resonators geöffnet zu werden.

11. Der Resonator gemäß Anspruch 6 und welcher ei-

nen Controller hat, welcher eingerichtet ist, um den zweiten Schalter (15) zu steuern, um geschlossen zu werden, um den Resonator vorzuladen, und während des Betriebs des Resonators geöffnet zu werden.

12. Der Resonator gemäß irgendeinem vorherigen Anspruch, wobei der erste Schalter (11) einen MEM-Schalter aufweist.

13. Der Resonator gemäß irgendeinem vorherigen Anspruch, welcher von Anspruch 6 abhängt, wobei der zweite Schalter (15) einen MEM-Schalter aufweist.

14. Ein integrierter Schaltkreis, welcher den Resonator gemäß irgendeinem vorherigen Anspruch aufweist.

15. Ein Verfahren zum Steuern des Resonators gemäß irgendeinem Anspruch 1 bis 13, welches den Schritt eines Steuerns des ersten Schalters (11) hat, um die erste geladene Elektrode vorzuladen.

Revendications

1. Résonateur comprenant un élément (10) vibrant et une première électrode (20) disposée de manière à faire vibrer l'élément en fonction d'un signal d'entrée (V_{IN}), et à générer un signal de sortie (I_{OUT}) en fonction de la vibration, au moins un élément parmi ladite première électrode et ledit élément vibrant étant agencé de manière à stocker une charge électrique au cours du fonctionnement du résonateur, ce par quoi au moins un élément parmi ladite première électrode et ledit élément vibrant comprend un dispositif d'ajustement de charge pour augmenter ou réduire la charge stockée,
et **caractérisé par le fait que** le dispositif d'ajustement de charge comprend une source de tension (8) raccordée par un premier commutateur (11) vers la première électrode (20) chargée ou l'élément (10) chargé, et **par le fait que** le premier commutateur (11) est agencé de manière à ce que la première électrode (20) chargée ou l'élément (10) chargé soit déconnecté de la source de tension (8) au cours du fonctionnement du résonateur.

2. Résonateur selon la revendication 1, le dispositif d'ajustement de charge comprenant un réservoir de charge couplé à la première électrode chargée ou à l'élément chargé.

3. Résonateur selon l'une quelconque des revendications 1 ou 2, la première électrode (20) chargée ou l'élément (10) chargé étant une électrode d'entrée (7) ou une électrode de sortie (4).

4. Résonateur selon la revendication 2, le réservoir de charge comprenant un condensateur de découplage (C) dans un circuit d'entrée ou de sortie vers ou à partir de l'électrode chargée.

5. Résonateur selon l'une quelconque des revendications précédentes, l'élément (10) vibrant étant raccordé électriquement à un substrat ou à une électrode de masse.

6. Résonateur selon la revendication 5, l'élément (10) vibrant étant raccordé électriquement au substrat ou à l'électrode de masse par l'intermédiaire d'un deuxième commutateur (15).

7. Résonateur selon l'une quelconque des revendications précédentes ayant une deuxième électrode (30) chargée.

8. Résonateur selon la revendication 7, ayant la première et la deuxième électrode (20, 30) chargée disposées sur les deux côtés de l'élément (10) vibrant.

9. Résonateur selon les revendications 7 ou 8, la deuxième électrode (30) chargée étant chargée sous une polarité différente.

10. Résonateur selon la revendication 1 et ayant un contrôleur agencé de manière à contrôler le premier commutateur pour qu'il soit fermé pour pré-charger le résonateur et qu'il soit ouvert au cours du fonctionnement du résonateur.

11. Résonateur selon la revendication 6 et ayant un contrôleur agencé de manière à contrôler le deuxième commutateur (15) pour qu'il soit fermé pour pré-charger le résonateur et qu'il soit ouvert au cours du fonctionnement du résonateur.

12. Résonateur selon l'une quelconque des revendications précédentes, le premier commutateur (11) comportant un commutateur MEM.

13. Résonateur selon l'une quelconque des revendications précédentes dépendant de la revendication 6, le deuxième commutateur (15) comportant un commutateur MEM.

14. Circuit intégré comprenant un résonateur selon l'une quelconque des revendications précédentes.

15. Procédé de commande d'un résonateur selon l'une quelconque des revendications 1 à 13, ayant l'étape consistant à commander le premier commutateur (11) pour pré-charger la première électrode chargée.

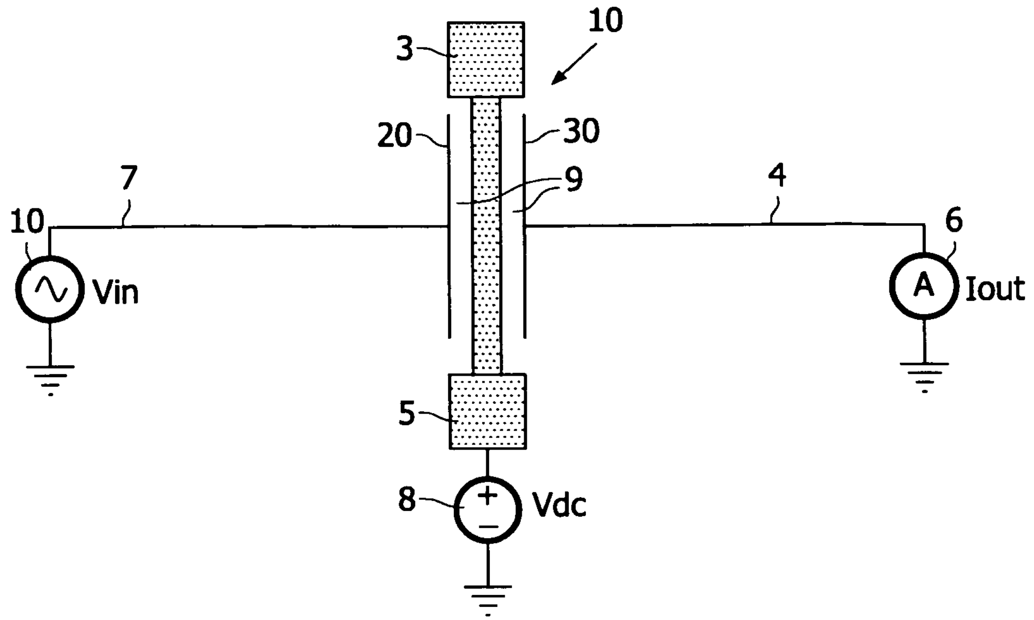

FIG. 1

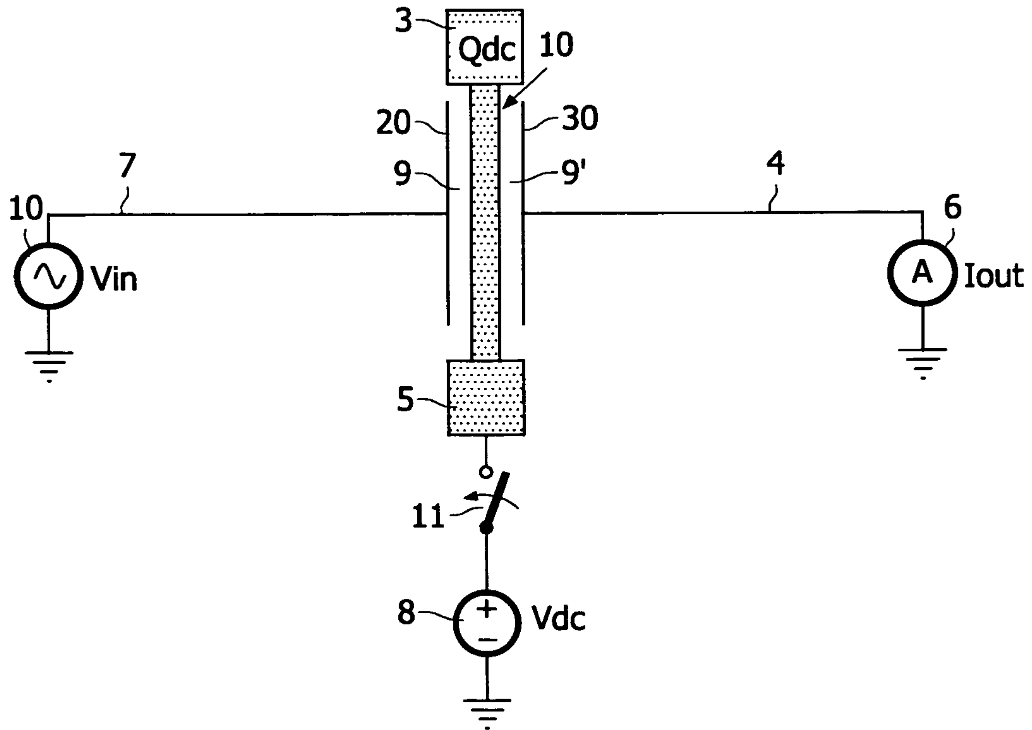

FIG. 2

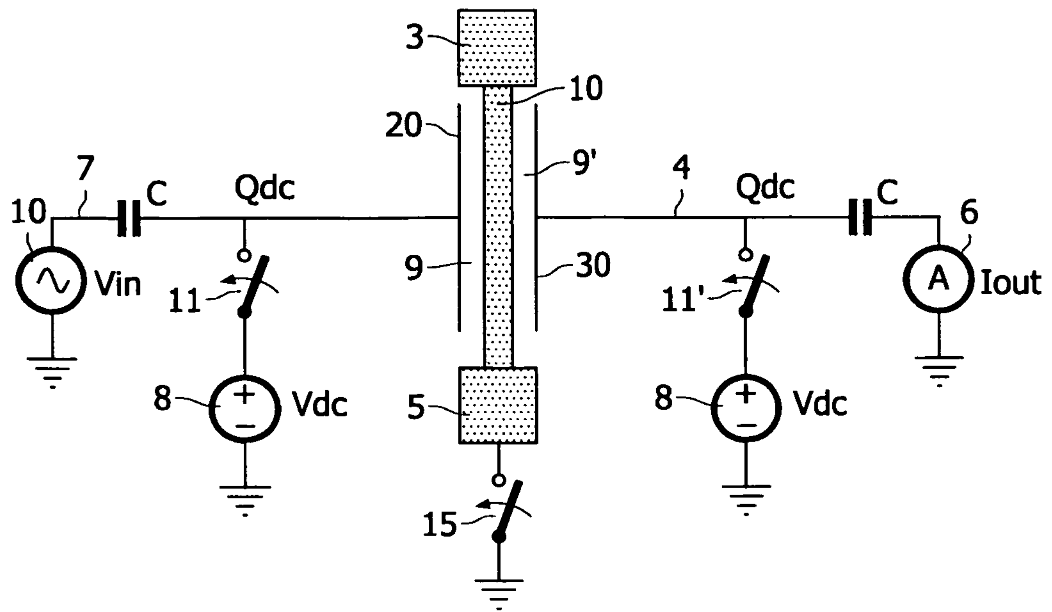

FIG. 3

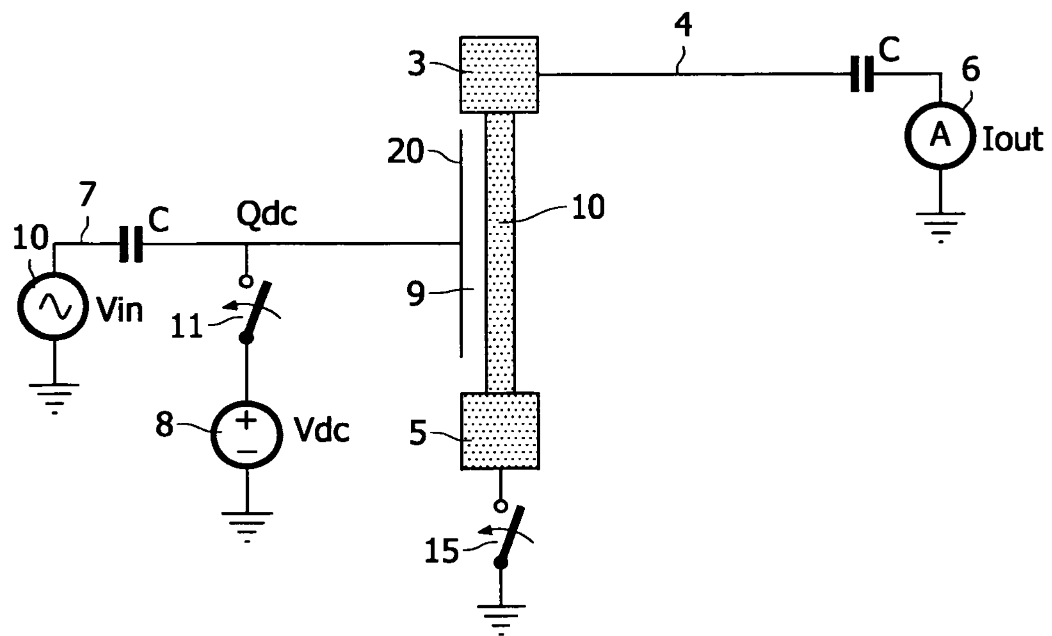

FIG. 4

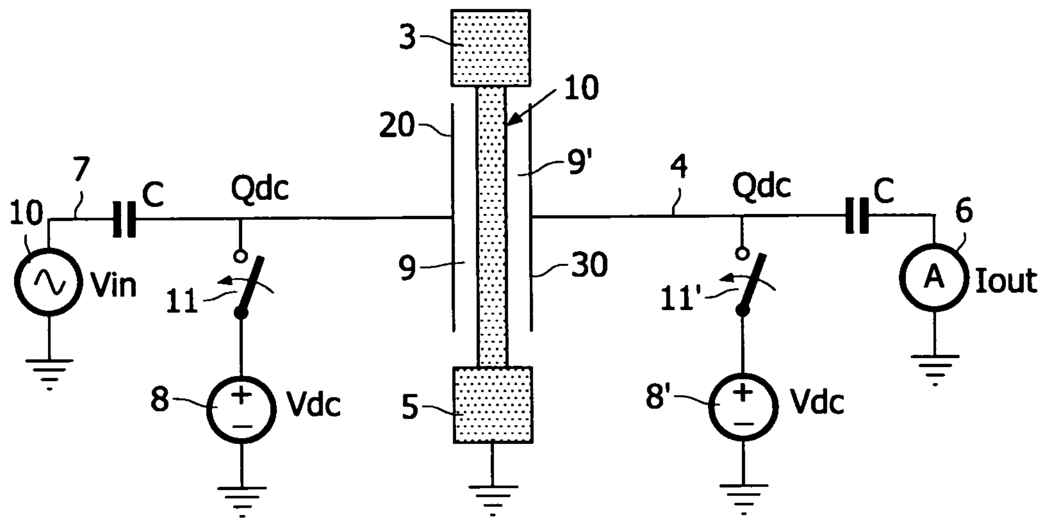

FIG. 5

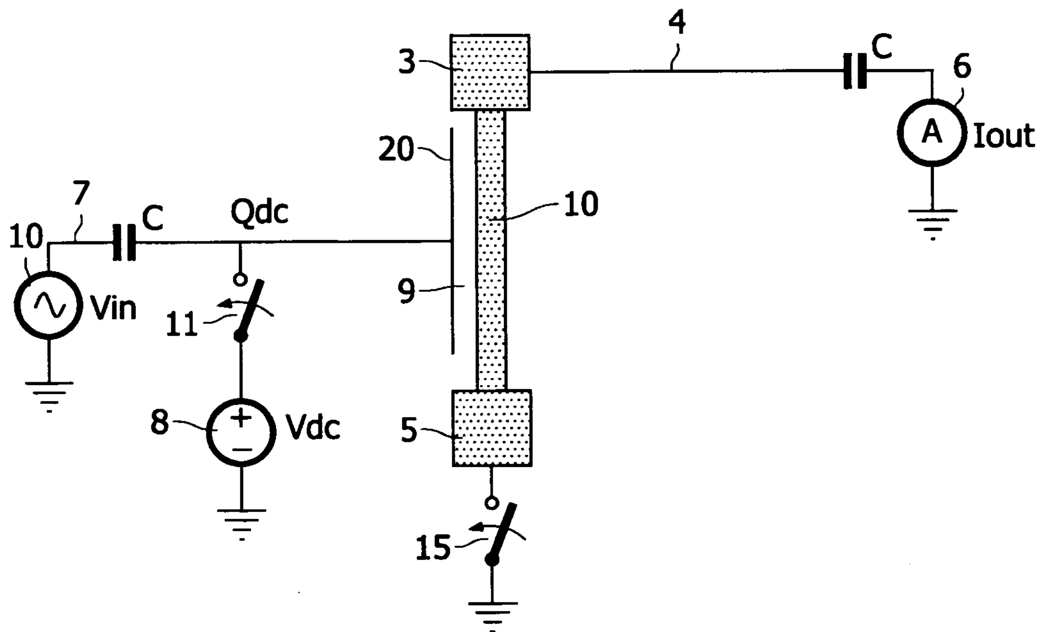

FIG. 6

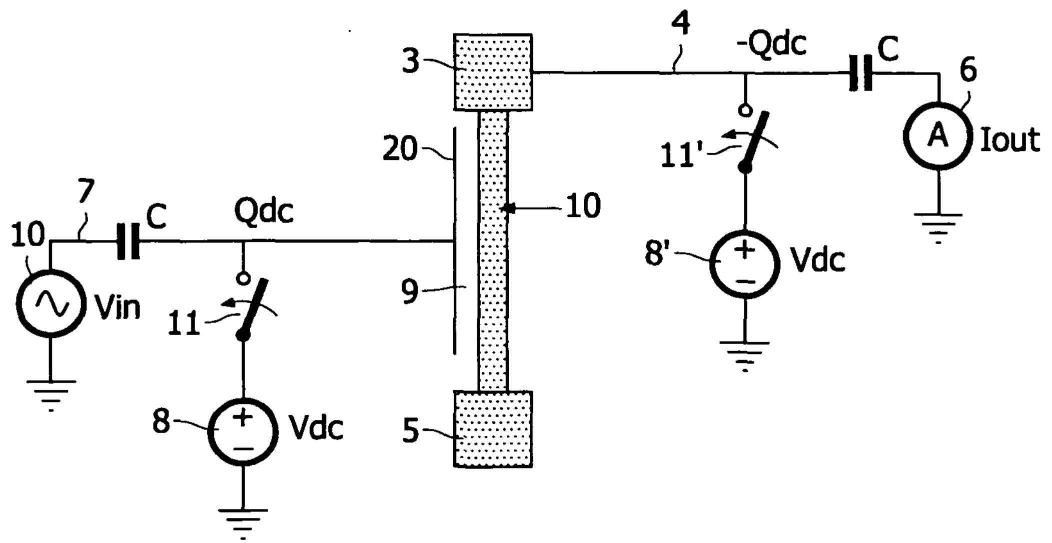

FIG. 7

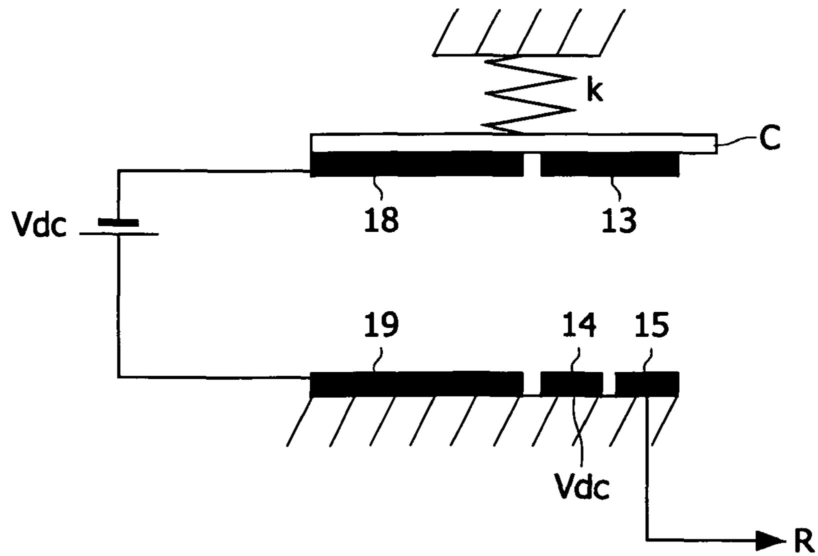

FIG. 8

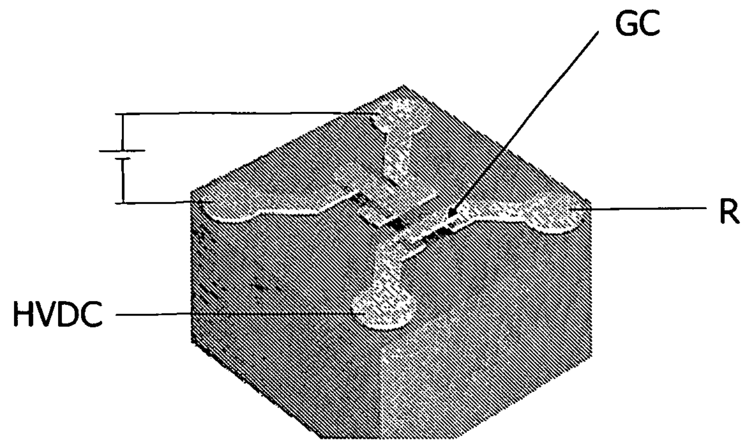

FIG.9

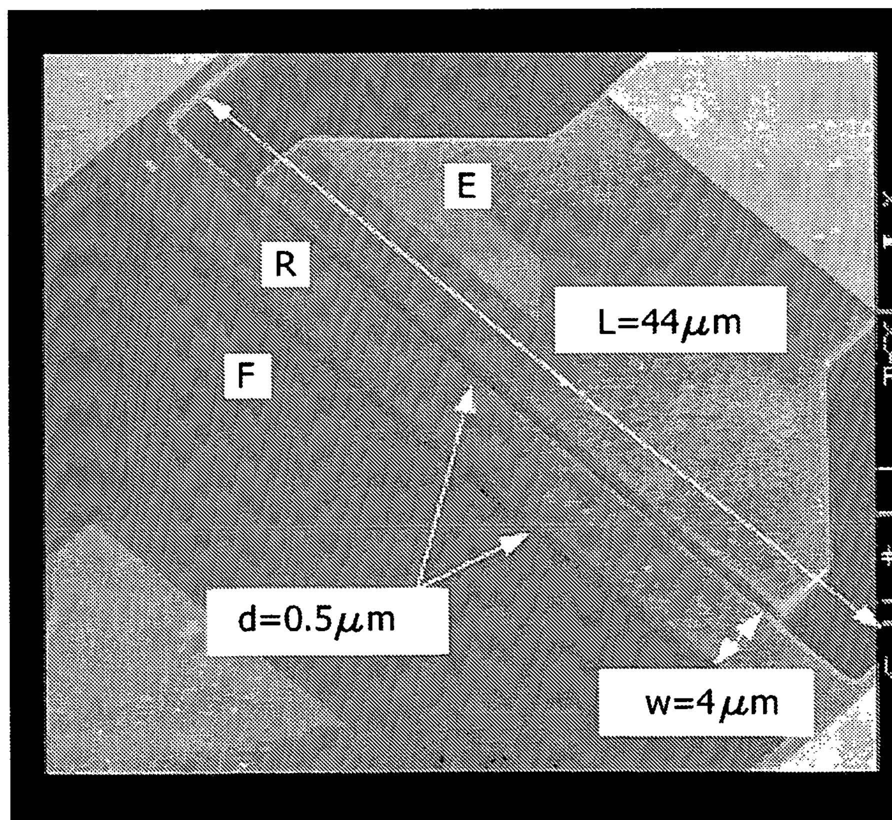

FIG.11

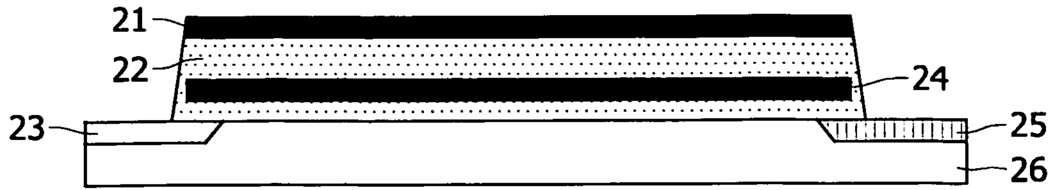

FIG. 10

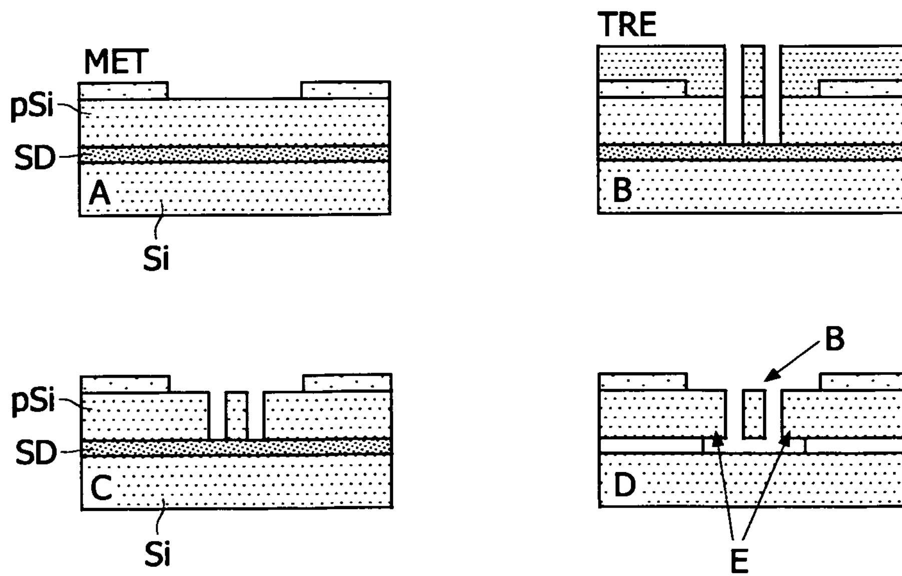

FIG. 12

REFERENCES CITED IN THE DESCRIPTION

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